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KOSHIBA & PART

NO. 6127 P. 2

#10/Translation
10/10/01
V. Vannell



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of

Akitaka KIMURA

Serial No.: 09/161,981

Filed: 29th September, 1998

Group Art Unit: 2812

Examiner: S. Mulpuri

For: SEMICONDUCTOR LAYER
FORMED BY SELECTIVE
DEPOSITION AND
METHOD FOR DEPOSITING
SEMICONDUCTOR LAYER

TRANSLATOR'S DECLARATION

Honorable Commissioner of Patents
and Trademarks
Washington, D. C. 20231

Sir:

I, Toyoaki SATOH, of 2F, Hirakawa-cho KS Bldg., 2-4-14, Hirakawa-cho, Chiyoda-ku, Tokyo 102-0093 JAPAN, hereby certify that I am conversant with both the Japanese and the English languages, and I have prepared the attached English translation of Japanese Patent Application No. Heisei 9-264225 filed on 29th September 1997, and that the English translation is a true, faithful and exact translation of the corresponding Japanese language document.

I further declare that all statements made in this declaration of my own knowledge are true and that all statements made on information and belief are believed to be true; and further, that these statements are made with the knowledge that willful, false statements and the like so made are punishable by fine or imprisonment, or both, under Section 1001 of Title 18 of the United States Code and that such willful, false statements may jeopardize the validity of this application or any Patent issued thereon.

September 27, 2001

Date

Name: Toyoaki SATOH

Patent Office

Japanese Government

This is to certify that the annexed is a true copy of the following application as filed with this office.

Date of Application: 29th September 1997
Application Number: Patent Application
No. 264225 of Heisei 9 (1997)
Applicant: NEC Corporation

10th April 1998

**Commissioner,
Patent Office**

Hisamitsu ARAI